METHOD OF FORMING PID PROTECTION DIODE FOR SOI WAFER

ABSTRACT

An integrated microelectronics semiconductor circuit fabricated on a silicon-on-insulator (SOI) type substrate can be protected from unwanted current surges and excessive heat buildup during fabrication by means of a heat-dissipating, protective plasma-induced-damage (PID) diode. The present invention fabricates such a protective diode as a part of the overall scheme in which the transistor devices are formed.

Figure 3